

THIS SHEET HAS BEEN
REPLACED

1 ABSTRACT

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3 METHOD OF DEPOSITION

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6 There is described a method of chemically depositing a
7 substance. The method is of utility in the direct
8 manufacture of integrated circuits and in the
9 manufacture of a photomask for use in production of
10 integrated circuits. The method involves the use of a
11 compound which degrades into a deposit and a residue
12 when a radiant beam (eg a laser beam) or a particle
13 beam (eg an electron beam) is applied. The residue and
14 any unreacted compound may be washed off the substrate
15 to which it has been applied. Nanoscale dimensions of
16 the deposit can be achieved. A particularly suitable
17 organometallic compound is tetra-sec butyl diaurum
18 difluoride.

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